

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-31. (Canceled)

32. (Currently Amended) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of first and second wirings is aligned with at least one edge portion of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the at least one edge portion of the active layer, and

~~wherein the second insulating film is in contact with the insulating surface~~

wherein a concentration of a catalyst element in the active layer of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

33. (Currently Amended) A semiconductor device comprising:
at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:
an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;
a gate insulating film over the active layer; and
a gate electrode over the gate insulating film,
a first insulating film over the thin film transistor;
first and second wirings connected to the active region through contact holes in the first insulating film,
a second insulating film over the first insulating film;
wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer,
wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge of the active layer, and
wherein the second insulating film is in contact with the insulating surface[.], and wherein a concentration of a catalyst element in the pair of impurity regions of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

34. (Currently Amended) A semiconductor device comprising:
at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:
an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;
a gate insulating film over the active layer; and
a gate electrode over the gate insulating film,
a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of the edge portions of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge portions of the active layer, and

wherein the second insulating film is in contact with the insulating surface[[.]], and
wherein a concentration of a catalyst element in the pair of impurity regions of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

35. (Currently Amended) A semiconductor device according to claim 32, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, [[an]] a rear projector and a front projector.

36. (Currently Amended) A semiconductor device according to claim 33, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, [[an]] a rear projector and a front projector.

37. (Currently Amended) A semiconductor device according to claim 34, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, [[an]] a rear projector and a front projector.

38. (Previously Presented) A semiconductor device according to claim 32, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

39. (Previously Presented) A semiconductor device according to claim 33, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

40. (Previously Presented) A semiconductor device according to claim 34, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

41. (New) A semiconductor device according to claim 32, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

42. (New) A semiconductor device according to claim 33, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

43. (New) A semiconductor device according to claim 34, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

44. (New) A semiconductor device comprising:
at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:
an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;
a gate insulating film over the active layer; and
a gate electrode over the gate insulating film,
a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of first and second wirings is aligned with at least one edge portion of the active layer, and

wherein a concentration of a catalyst element in the active layer of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

45. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer, and

wherein a concentration of a catalyst element in the pair of impurity regions of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

46. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of the edge portions of the active layer, and

wherein a concentration of a catalyst element in the pair of impurity regions of the at least one p-channel thin film transistor is lower than that of the at least one n-channel thin film transistor.

47. (New) A semiconductor device according to claim 44, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

48. (New) A semiconductor device according to claim 45, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

49. (New) A semiconductor device according to claim 46, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

50. (New) A semiconductor device according to claim 44, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

51. (New) A semiconductor device according to claim 45, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

52. (New) A semiconductor device according to claim 46, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

53. (New) A semiconductor device according to claim 44, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

54. (New) A semiconductor device according to claim 45, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

55. (New) A semiconductor device according to claim 46, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

56. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of at least one of first and second wirings is aligned with at least one edge portion of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the at least one edge portion of the active layer, and

wherein the pair impurity regions of the at least one n-channel thin film transistor have a catalyst element in a concentration of 5×10^{18} atoms/cm³ or more.

57. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of one of the first and second wirings is aligned with an edge of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge of the active layer,

wherein the second insulating film is in contact with the insulating surface, and

wherein the pair impurity regions of the at least one n-channel thin film transistor have a catalyst element in a concentration of 5×10^{18} atoms/cm³ or more.

58. (New) A semiconductor device comprising:

at least one p-channel thin film transistor and at least one n-channel thin film transistor, each comprising:

an active layer comprising a pair of impurity regions and a channel region between the pair of impurity regions over an insulating surface;

a gate insulating film over the active layer; and

a gate electrode over the gate insulating film,

a first insulating film over the thin film transistor;

first and second wirings connected to the active region through contact holes in the first insulating film,

a second insulating film over the first insulating film;

wherein a part of an edge portion of the first wiring is aligned with one of edge portions of the active layer, and a part of an edge portion of the second wiring is aligned with another one of the edge portions of the active layer,

wherein the gate insulating film is in contact with the first and second wirings and not in contact with the edge portions of the active layer,

wherein the second insulating film is in contact with the insulating surface, and

wherein the pair impurity regions of the at least one n-channel thin film transistor have a catalyst element in a concentration of 5×10^{18} atoms/cm³ or more.

59. (New) A semiconductor device according to claim 56, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

60. (New) A semiconductor device according to claim 57, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

61. (New) A semiconductor device according to claim 58, wherein the semiconductor device is a device selected from the group consisting of a portable telephone, a video camera, a mobile computer, a goggle type display, a rear projector and a front projector.

62. (New) A semiconductor device according to claim 56, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

63. (New) A semiconductor device according to claim 57, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

64. (New) A semiconductor device according to claim 58, wherein the second insulating film comprises a material selected from the group consisting of silicon nitride, silicon oxide and silicon nitride oxide.

65. (New) A semiconductor device according to claim 56, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

66. (New) A semiconductor device according to claim 57, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.

67. (New) A semiconductor device according to claim 58, wherein the catalyst element is selected from the group consisting of Ni, Co, Fe, Pd, Pt, Cu and Au.